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# EE4280 Lecture 2: Mismatch

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# Mismatch (I)

$W_0 = 1\mu m$  Even with one single device

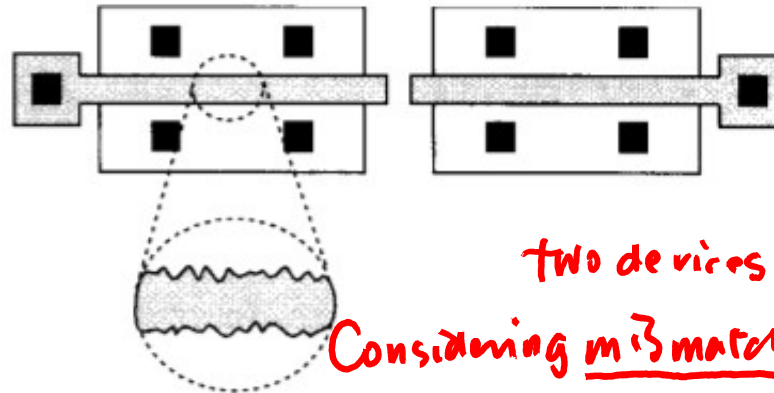
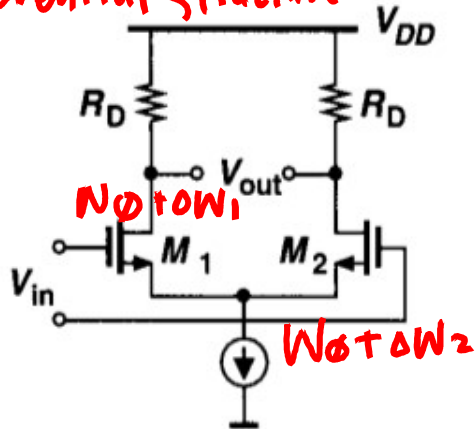
Due to uncertainties in each step of the manufacturing process  
 For identical devices, random and microscopic variations lead to

- Mismatches in physical dimension
- Mismatches in threshold voltages

$W_1, W_2, W_3, \dots, W_{3m}$   
 $W_0 + \Delta W_1, W_0 + \Delta W_2 \rightarrow \Delta W_{rms}^2$

over the entire sample space

differential structure



two devices involved

Considering mismatch  $\Delta W_{12}$

$$\Delta W_{12} = (W_1 - W_2) = \Delta W_1 - \Delta W_2$$

$$\overline{\Delta W_{12}} = 0$$

$$\overline{\Delta W_{12}^2} = \overline{(\Delta W_1 - \Delta W_2)^2}$$

To study mismatch of devices:

1. Identify and formulate the mechanisms leading to mismatches
2. Analyze the impact on circuit performance  $= \text{avg}(\Delta W_{12}^2)$

→ Techniques to suppress the impact from mismatches

$$= 2 \cdot \Delta W_{rms}^2 - 2 \cdot \overline{\Delta W_1 \Delta W_2}$$

$$\sigma_{W_{12}, \text{rms}}^2 = 2 \cdot \sigma_{W, \text{rms}}^2 = 2 \cdot \overline{\sigma_{W_1} \cdot \sigma_{W_2}}$$

★

for  $\overline{\sigma_{W_1} \cdot \sigma_{W_2}}$ : if  $M_1$  and  $M_2$  are totally uncorrelated

$$\overline{\sigma_{W_1} \cdot \sigma_{W_2}} = 0$$

$$\sigma_{W_{12}, \text{rms}} = \sqrt{2} \cdot \sigma_{W, \text{rms}}$$

What if we can increase the correlation between the two

so that  $\overline{\sigma_{W_1} \cdot \sigma_{W_2}} \rightarrow \overline{\sigma_{W_1}^2}$

then  $\sigma_{W_{12}, \text{rms}}^2 \rightarrow 0$

# Mismatch (II)

For a transistor operating in saturation region

$$I_D = \frac{1}{2} \mu C_{ox} \frac{W}{L} (V_{GS} - V_{th})^2$$

$$\sigma_{LB} = \frac{\sigma_{L1} + \sigma_{L2}}{2}$$

$$\overline{\sigma_{LB}^2} = \frac{1}{4} (\overline{\sigma_{L1}^2} + \overline{\sigma_{L2}^2} + \underbrace{2\sigma_{L1}\sigma_{L2}}_{\text{wavy line}})$$

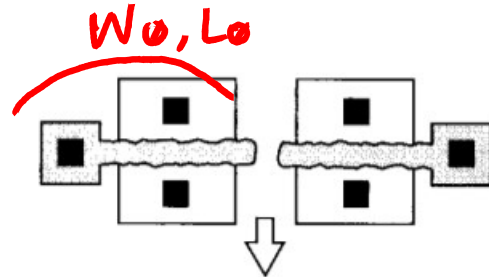
$(2\sigma_{L1}\sigma_{L2} \rightarrow \emptyset)$   
 $\sigma_{LB, rms} = \frac{1}{\sqrt{2}} \sigma_{LA, rms}$

Device #A

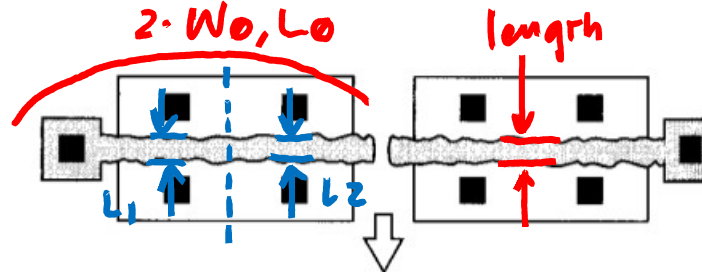
Device #B

All mismatches decreases as the area of the transistor  $WL$  increases

- Random variations experience greater averaging  $\star$  if  $L_1$  &  $L_2$  uncorre.



$$L_A = L_0 + \sigma_{LA}$$



$$L_B = L_0 + \sigma_{LB}$$

$$= \frac{L_1 + L_2}{2} = \frac{L_0 + \sigma_{L1} + L_0 + \sigma_{L2}}{2}$$

$$= L_0 + \frac{\sigma_{L1} + \sigma_{L2}}{2}$$

depends on factory

Can be extended to other device parameters

$$\frac{\Delta V_{TH}}{V_{TH}} = \frac{A_{VTH}}{\sqrt{WL}} \quad \Delta \left( \mu C_{ox} \frac{W}{L} \right) = \frac{A_K}{\sqrt{WL}}$$

$\sigma_{LB}$ , error of the wider tran.

$\star$  if  $L_1$  &  $L_2$  highly corre.

then  $L_1 = L_2$

$$\rightarrow \sigma_{LB, rms} = \sigma_{LA, rms}$$

# DC Offset

non-zero error



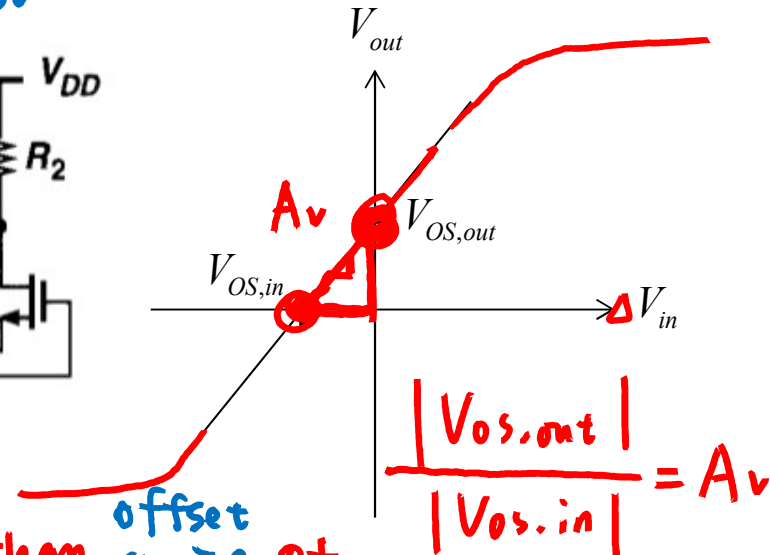
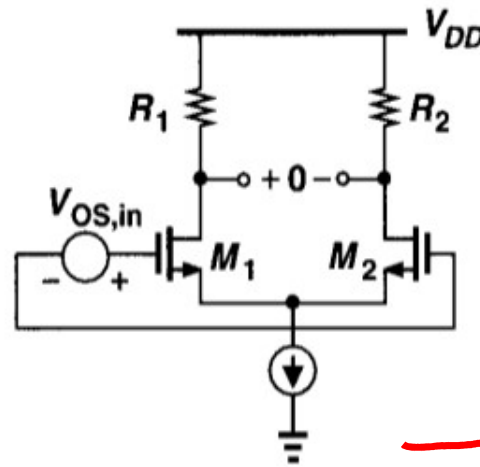
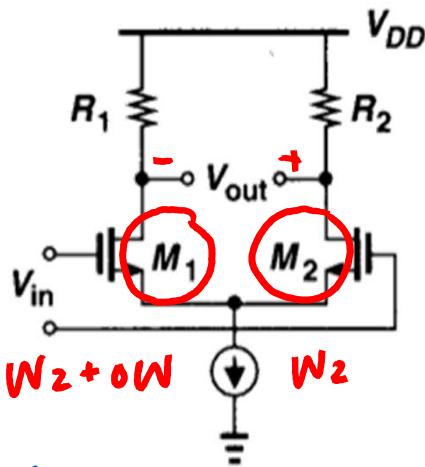
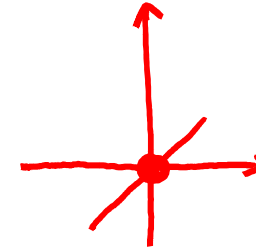
With perfect symmetry  $V_{out} = 0$  when  $V_{in} = 0$

amplifier chain

With mismatches  $V_{OS,out} \neq 0$  when  $V_{in} = 0$

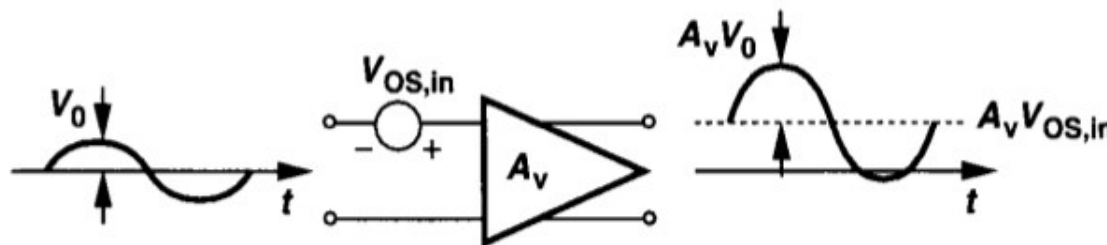
noise offset

linearity

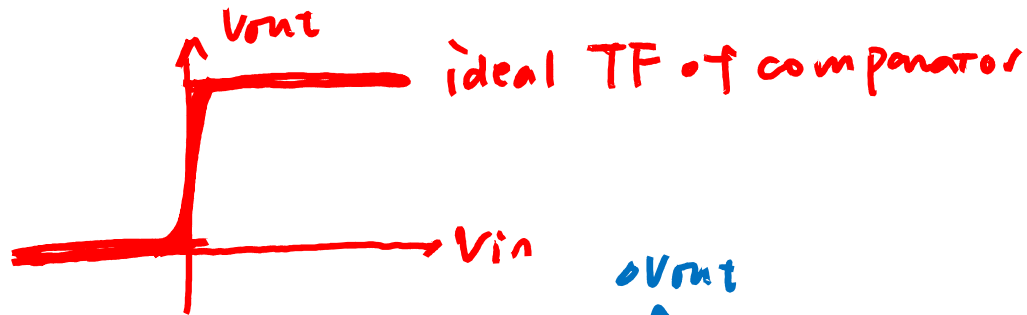
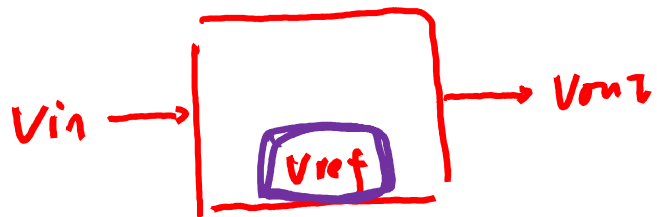


offset/noise in the first amp. is more critical than offset/noise of the following stages

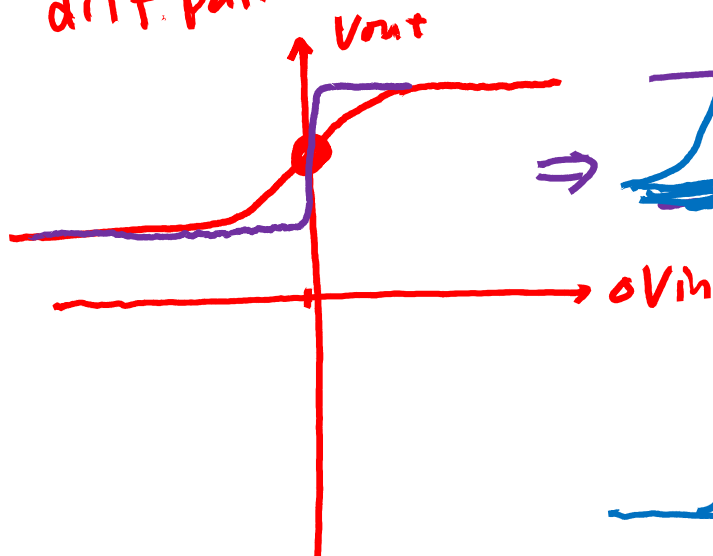
- May saturate the following stages
- Degrade the precision with which signals can be measured



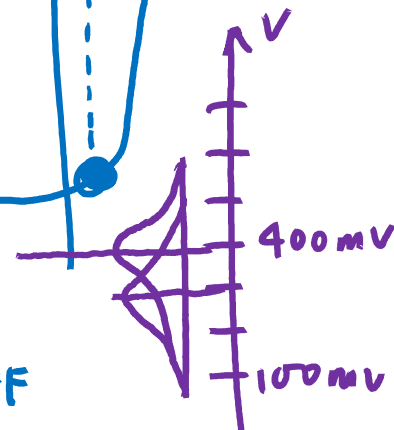
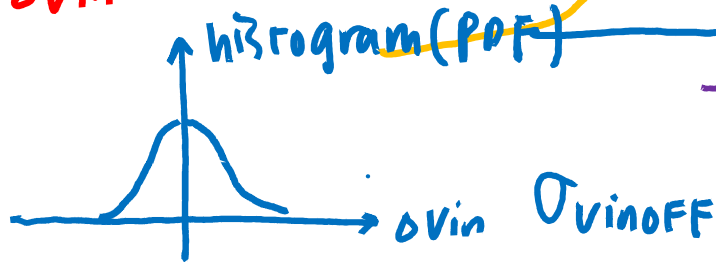
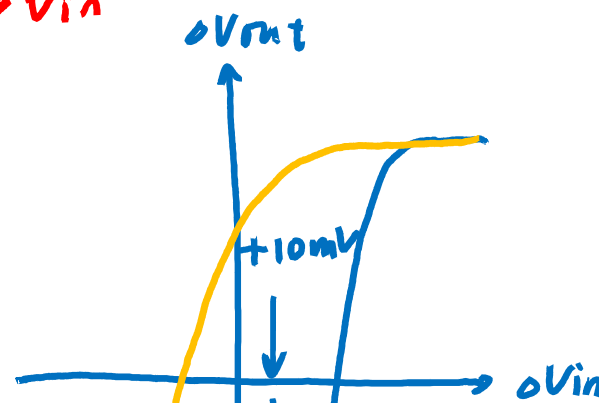
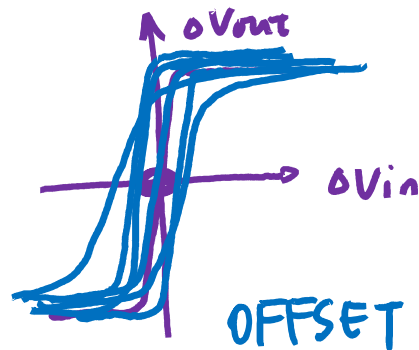
# Comparator (ADC, mixed-signal ckt)



high-gain amplifier  
diff. pair

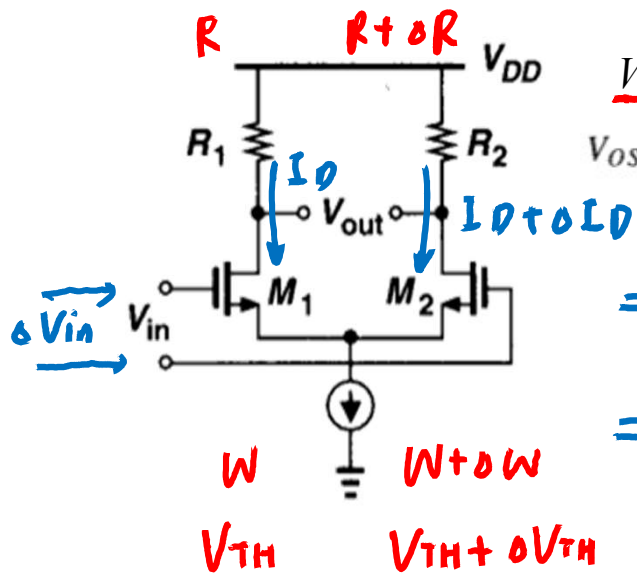


$V_{ref} = 0$



# DC Offset of a differential pair

- ◆ To calculate the input-referred offset



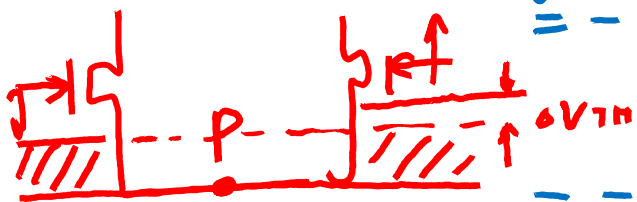
$$V_{out} = 0 \Rightarrow I_D R_D = (I_D + \Delta I_D)(R_D + \Delta R) = I_D \cdot R_D \left(1 + \frac{\Delta I}{I}\right) \left(1 + \frac{\Delta R}{R}\right)$$

$$V_{OS, in} = V_{GS1} - V_{GS2}$$

$$\approx I_D R_D \left(1 + \frac{\Delta I}{I} + \frac{\Delta R}{R}\right)$$

$$= V_{TH1} + V_{ov1} - (V_{TH2} + V_{ov2}) \Rightarrow \frac{\Delta I}{I} = -\frac{\Delta R}{R}$$

$$= -\Delta V_{TH} + \sqrt{\frac{I_{D1}}{\mu C_{ox} \left(\frac{W}{L}\right)_1}} - \sqrt{\frac{(I_D + \Delta I)}{\mu C_{ox} \left(\frac{W}{L} + \Delta \frac{W}{L}\right)}}$$



$$\approx -\Delta V_{TH} + \sqrt{\frac{I_D}{\mu C_{ox} \left(\frac{W}{L}\right)} \cdot \left(1 - \left(1 + 0.5 \frac{\Delta I}{I}\right) \left(1 - 0.5 \frac{\Delta W}{W}\right)\right)}$$

$$= -\Delta V_{TH} + \sqrt{\frac{I_D}{\mu C_{ox} \left(\frac{W}{L}\right)} \left(-0.5 \frac{\Delta I}{I} + 0.5 \frac{\Delta W}{W}\right)}$$

$$= -\Delta V_{TH} + \frac{V_{ov}}{2} \left(\frac{\Delta W}{W} - \frac{\Delta I}{I}\right) \Rightarrow -\Delta V_{TH} + \frac{V_{ov}}{2} \left(\frac{\Delta W}{W} + \frac{\Delta R}{R}\right)$$

# DC Offset of a differential pair

- ◆ To calculate the input-referred offset

$$\overline{V_{OS,in}^2} = \left( \frac{V_{GS} - V_{TH}}{2} \left[ \frac{\Delta R_D}{R_D} + \frac{\Delta(W/L)}{(W/L)} - \Delta V_{TH} \right] \right)^2$$

①  $\Delta V_{TH}$  has a direct impact on  $V_{OS,in}$

- Depends on device mismatches and bias conditions
- ◆ Offset can be viewed as low-frequency noise
- Similar to noise, larger  $g_{m1}$  suppresses input-referred offset voltage

②  $V_{ov} \downarrow$   
 $W/L \uparrow$   
 $g_m \uparrow$

We want

- ◆ Variance:

$$V_{OS,in,rms} = \sqrt{\left( \frac{V_{ov}}{2} \left( \frac{\Delta R_{rms}}{R_D} \right) \right)^2 + \left( \frac{V_{ov}}{2} \right)^2 \left( \frac{\Delta W_{rms}}{W} \right)^2 + \Delta V_{TH,rms}^2}$$

↑  
Sample Space

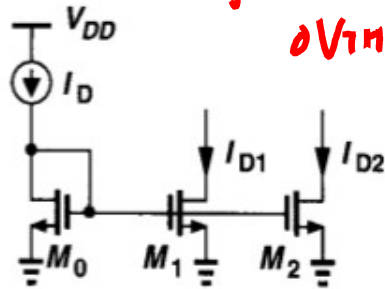
- ◆ Consider only transistor mismatch, for  $I_{D1} = I_{D2}$



# Current mismatch in current mirror ★

- Consider nominally identical transistors ( $M_1$  and  $M_2$ ) and neglect  $r_o$

Goal: Calculate  $\frac{\Delta I}{I}$   
 as a result of  $\Delta W$ .



$W$      $W + \Delta W$   
 $V_{TH}$      $V_{TH} + \Delta V_{TH}$   
 $I_D$      $I_D + \Delta I$   
 (REF)

$$I_D = \frac{1}{2} \mu C_{ox} \frac{W}{L} (V_{GS} - V_{th})^2$$

$$= f\left(\mu C_{ox}, \frac{W}{L}, V_{GS}, V_{th}\right)$$

total differential

$$\Delta y = \frac{\partial f}{\partial x_1} \Delta x_1 + \frac{\partial f}{\partial x_2} \Delta x_2 + \dots$$

$$\Delta I_D = \frac{\partial I_D}{\partial (W/L)} \Delta \left(\frac{W}{L}\right) + \frac{\partial I_D}{\partial (V_{GS} - V_{TH})} \Delta (V_{GS} - V_{TH})$$

(gain) sensitivity of cur. to  $W$ .

- From output current point of view

- Smaller  $g_m$  required to suppress the mismatch
- The same for noise current

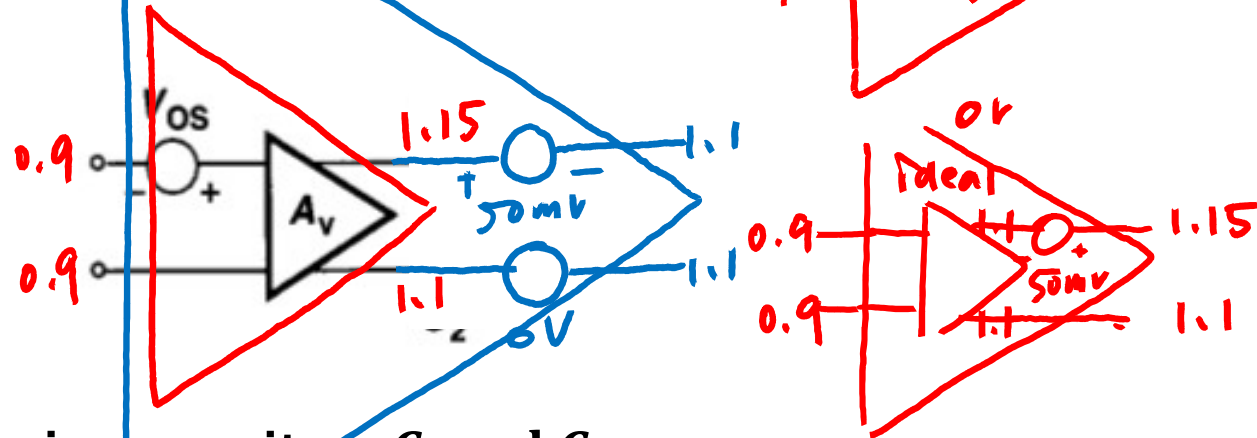
$$\Delta I = \left(\frac{1}{2} \mu C_{ox} V_{ov}^2\right) \cdot \Delta \left(\frac{W}{L}\right) + \left(\mu C_{ox} \frac{W}{L} V_{ov}\right) \cdot \Delta V_{ov}$$

$$\Rightarrow \frac{\Delta I}{I} = \frac{\Delta \left(\frac{W}{L}\right)}{\left(\frac{W}{L}\right)} - 2 \frac{\Delta V_{TH}}{V_{ov}}$$

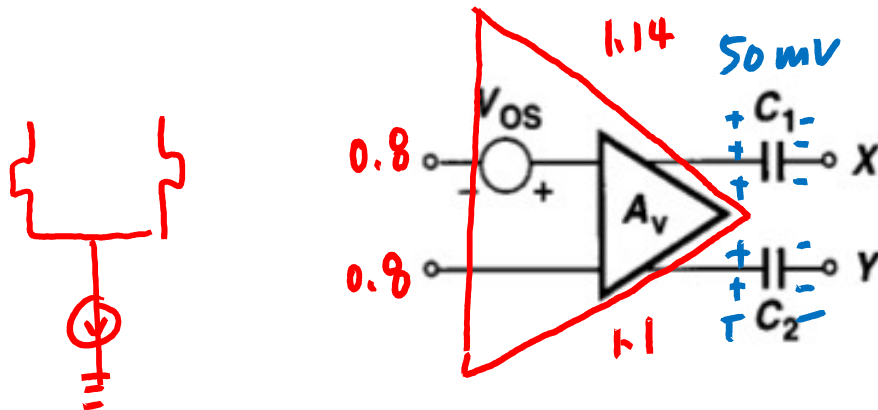
size err. impact directly on  $\Delta I$

# Offset Cancellation Techniques

- ◆ Add two voltage sources in series with  $V_{out}$

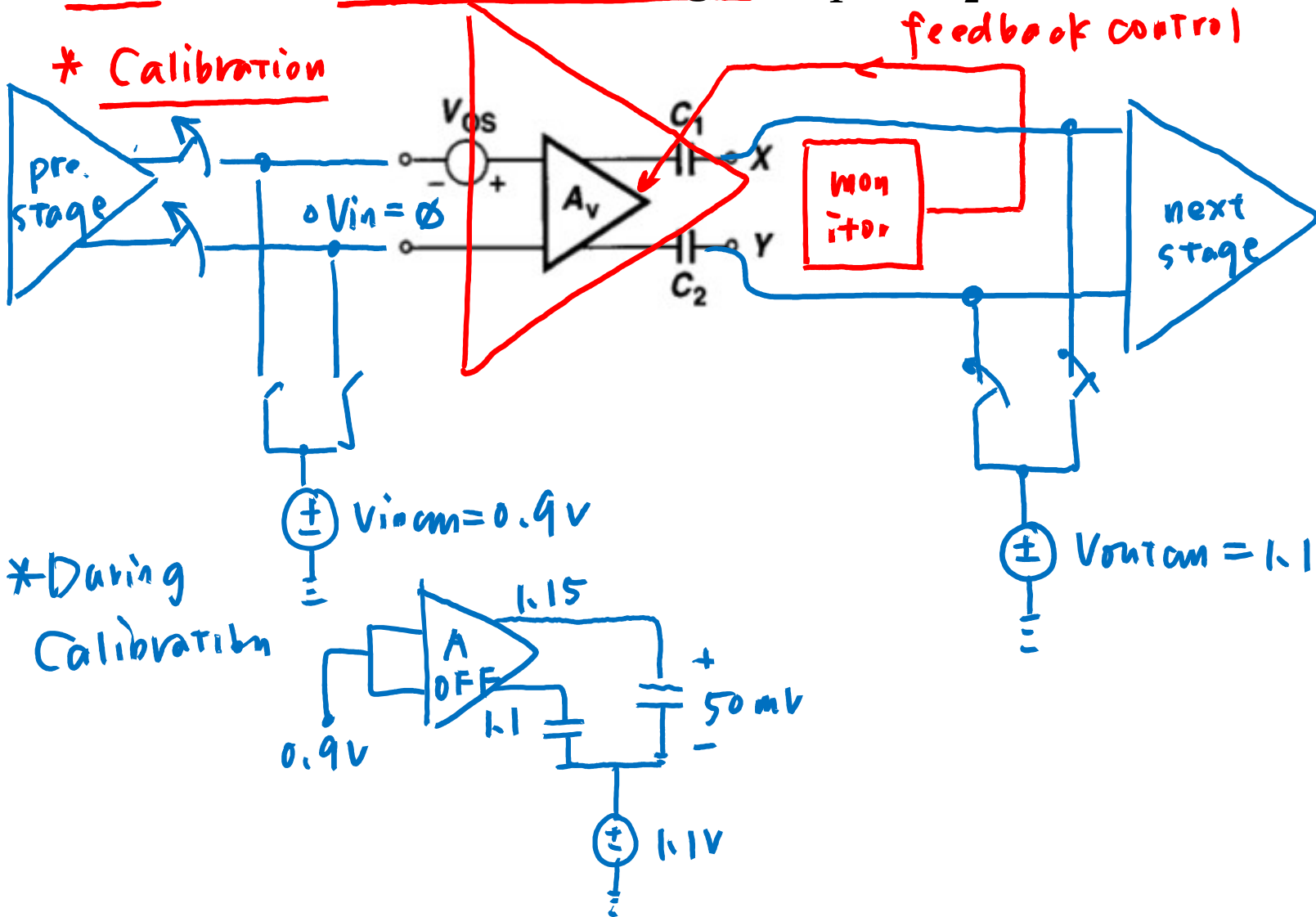


- ◆ Use output series capacitors  $C_1$  and  $C_2$ 
  - With stored charges that corresponds to  $V_{OS,out}$

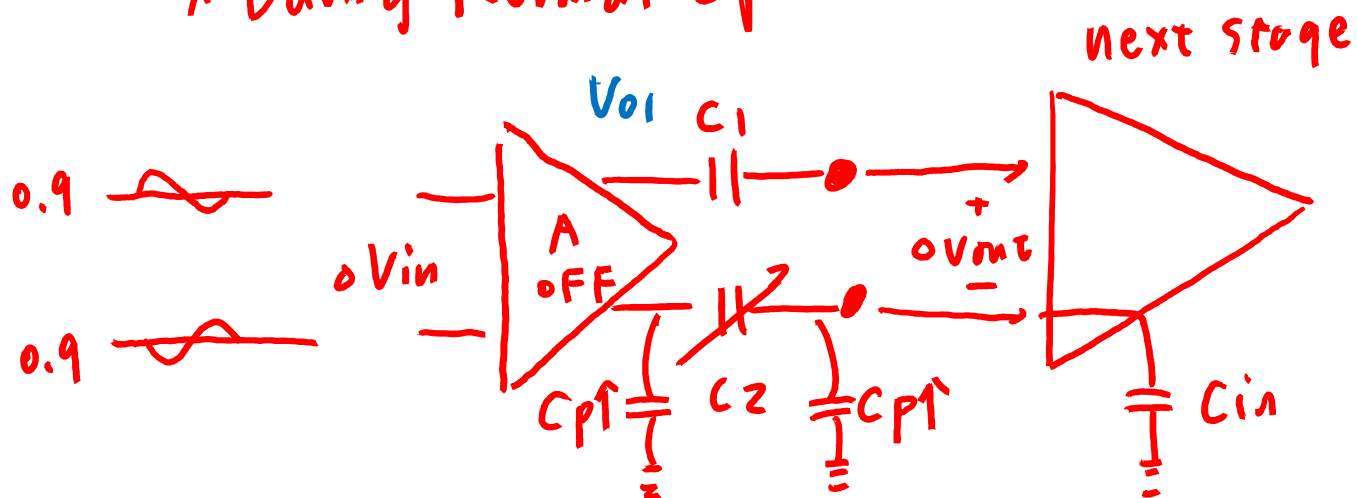


# Output Offset Storage

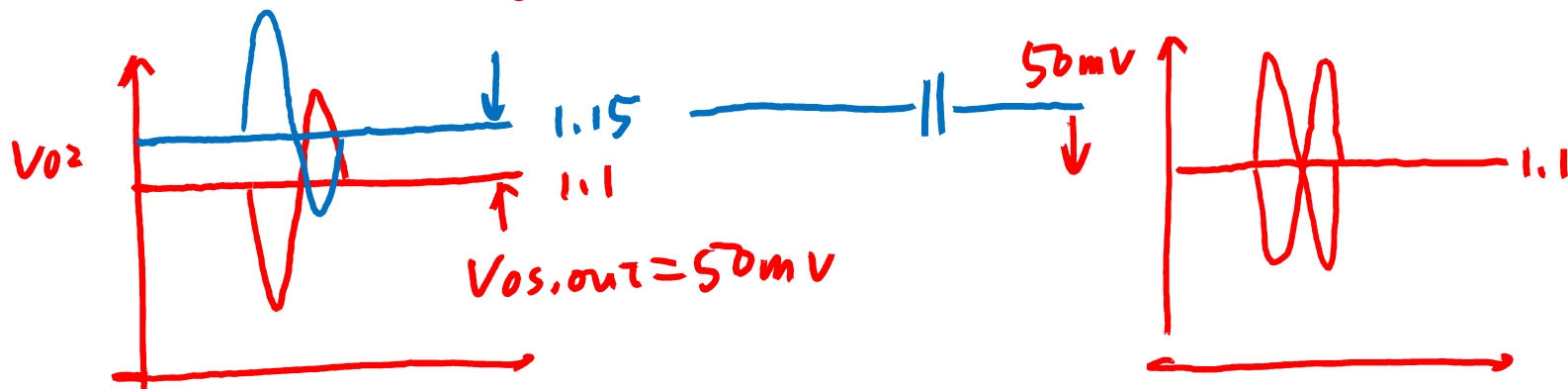
- ◆ How to store the required charge on  $C_1$  and  $C_2$ ?




# \* During Normal Operation

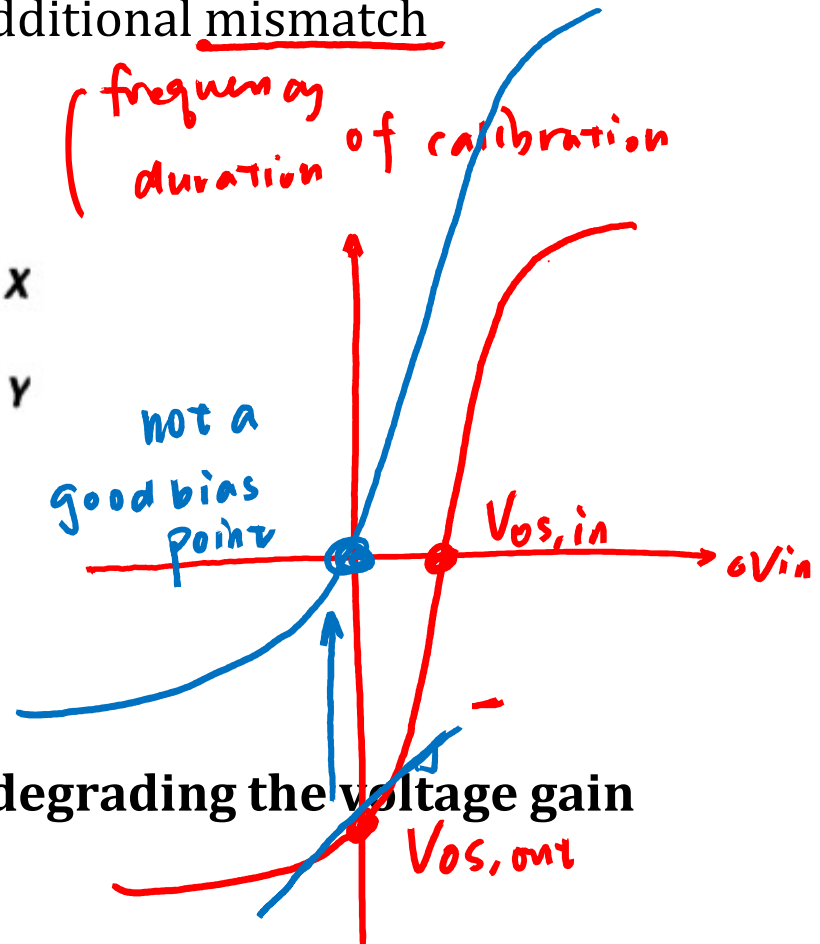
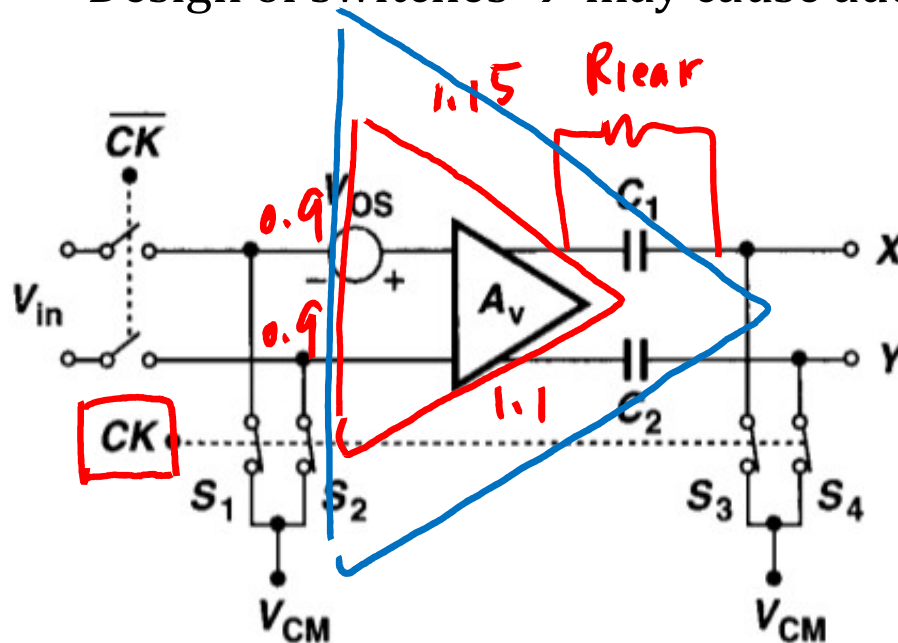


$$\frac{0V_{out}}{0V_{in}} = A \frac{C_2}{C_2 + C_{in}}$$



# Output Offset Storage

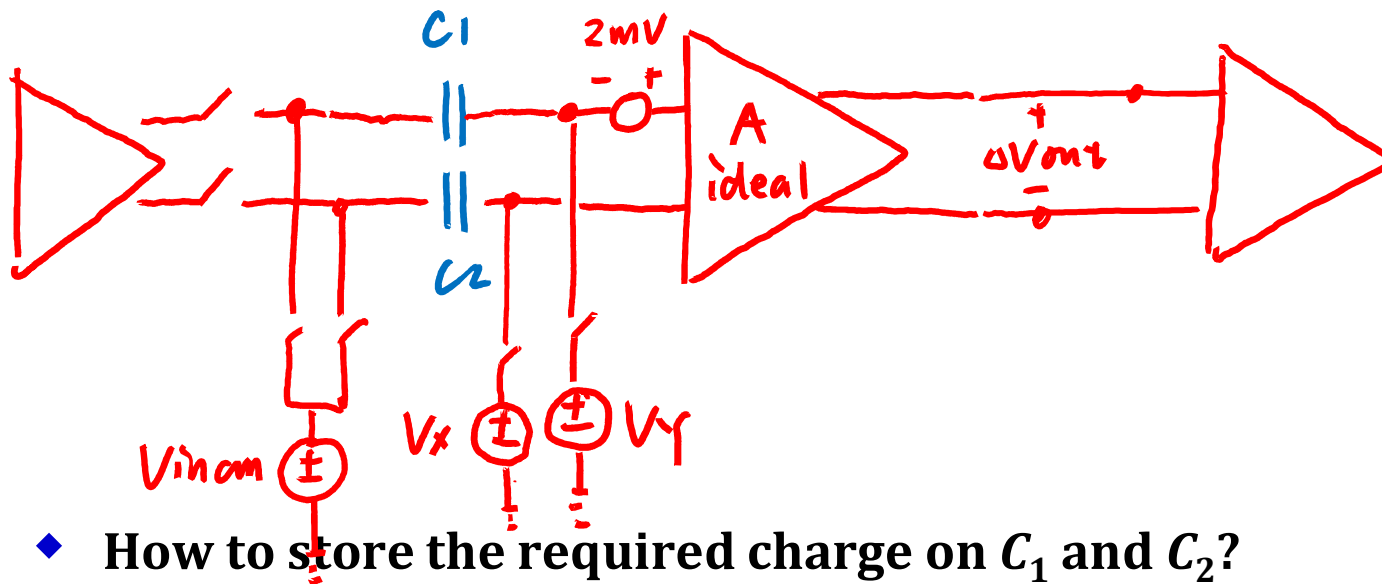
- ◆ A dedicated offset cancellation period required
  - Controlled by signal  $CK$   → two-phase operation
  - Design of switches → may cause additional mismatch



- ◆  $V_{OS,out}$  may saturate the amplifier, degrading the voltage gain

# Input Offset Storage

- ◆ The concept of using series capacitors to store offset voltage can be applied to input (with smaller voltage value)



- ◆ How to store the required charge on  $C_1$  and  $C_2$ ?

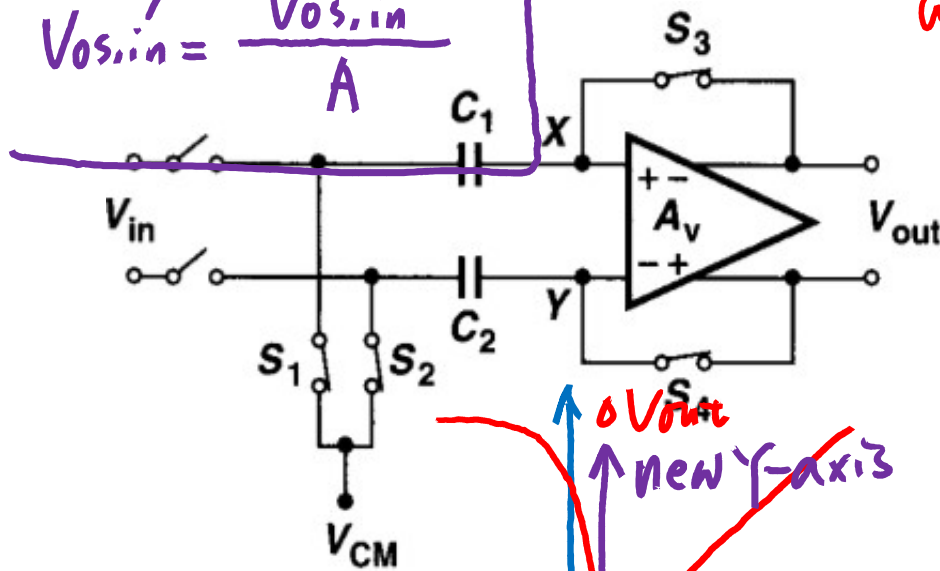
- ① the previous method doesn't work  
 $\because$  node X & Y are high- $Z$  nodes
- ② Adjust  $V_x$  and  $V_y$  until  $\Delta V_{out} = 0$

# Input Offset Storage ③

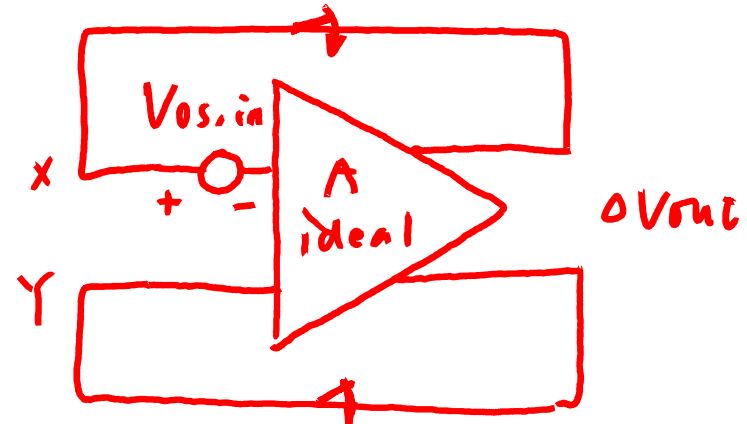
## During Calibration

- How to store the required charge on  $C_1$  and  $C_2$ ?

$$V_{OS,in}' = \frac{V_{OS,in}}{A}$$



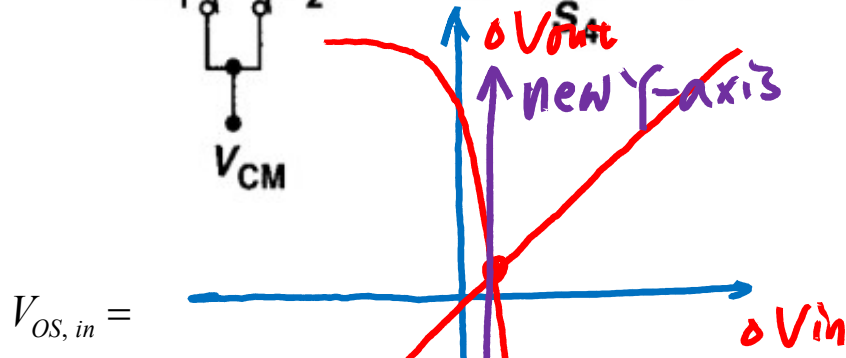
wait until the circuit settles



$$V_{XY} = \Delta V_{out} = \frac{A}{1+A} V_{OS,in} \cong V_{OS,in}$$

for the core part

$$\Delta V_{out} = -A (V_{XY} - V_{OS,in})$$

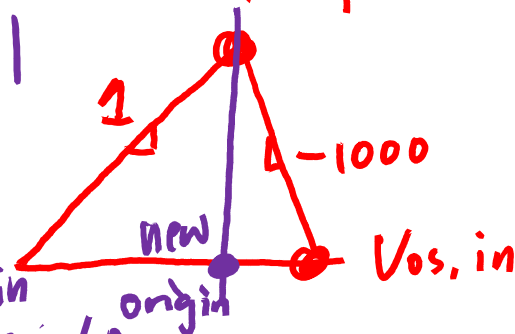


Back to Normal

- Allows larger  $A_V$
- Still subject to switches mismatch
- Additional capacitors in the signal path

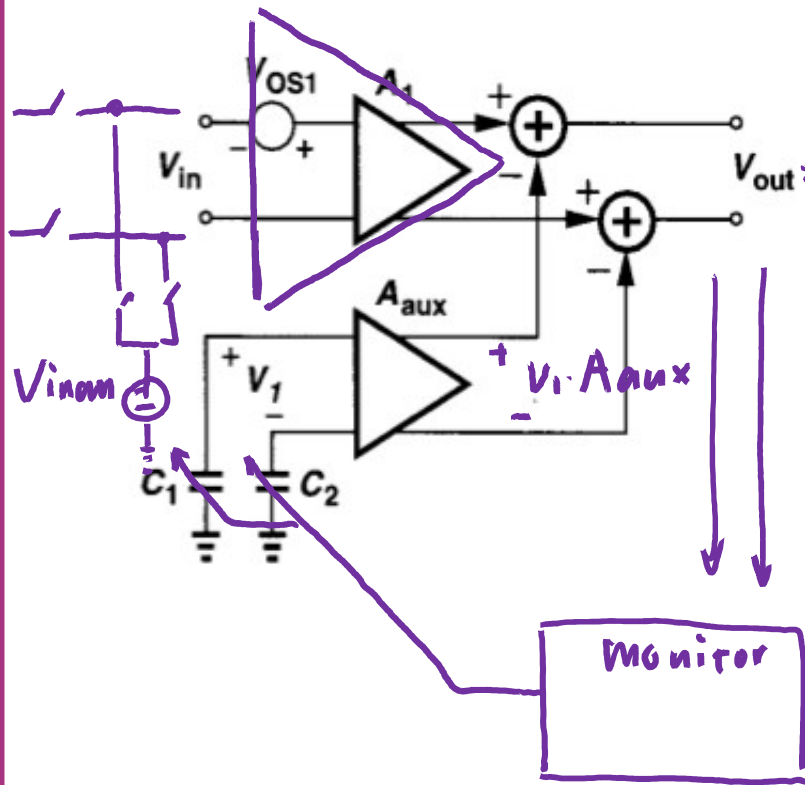
$$\Delta V_{in} = 0, \Delta V_{out} = V_{OS,in}$$

$$\Delta V_{OS,in}' = V_{OS,in}/A$$



# Offset Cancellation Techniques

- ◆ To avoid capacitors in the signal path



Output off. of the core amplifier

$$V_{out} = V_{OS1} \cdot A_1 - V_1 \cdot A_{aux} \rightarrow 0$$

Q1: How to implement the subtractor

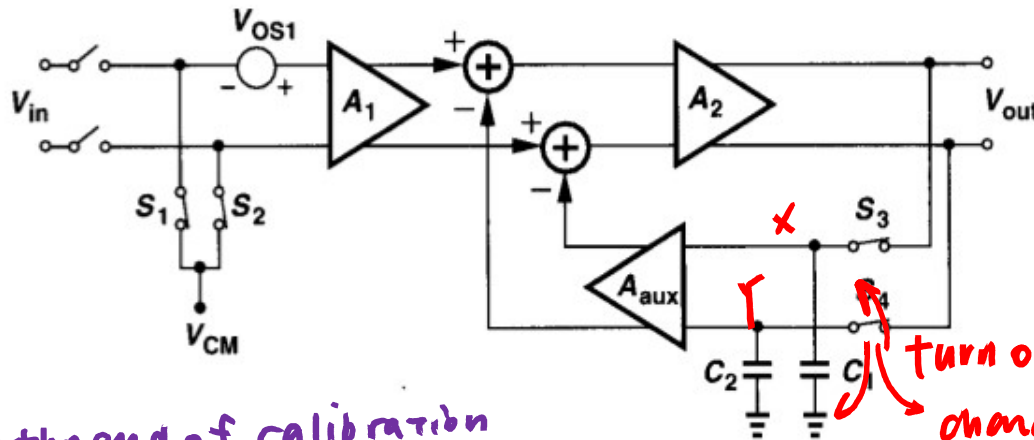
Q2: How to perform calibration

- ◆ How to generate  $V_1$  for offset cancellation?



# Offset Cancellation Techniques

- ◆ Add an additional stage  $A_2$  and apply negative feedback



Q1: How to impl the subtractor

@ the end of calibration

$$\text{with } \delta V_{in} = 0, \delta V_{out} = \frac{V_{OS1} \cdot A_1 \cdot A_2}{1 + A_2 \cdot A_{aux}}$$

nodes x and y are

high-z after turning off S3,4

then we turn off S3, S4

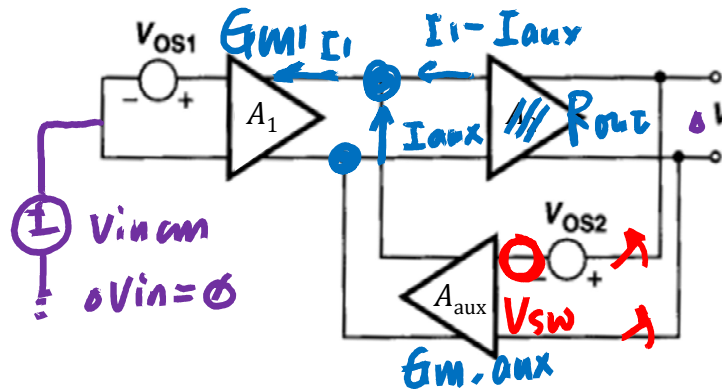
when setting back to normal operation

$$V_{OS, in, eff} = \frac{V_{OS1} A_1 A_2}{1 + A_2 \cdot A_{aux}} \frac{1}{A_1 \cdot A_2} \approx \frac{V_{OS1}}{A_2 \cdot A_{aux}} \leftarrow \text{loop gain FB}$$

# Offset Cancellation Techniques

$A_1$ : the subtraction can be performed in cur. domain

- ◆ If we further consider the offset in  $A_{aux}$



$$V_{out} = \frac{V_{os1} \cdot A_1 \cdot A_2}{1 + A_2 \cdot A_{aux}} + V_{os2} \frac{A_2 \cdot A_{aux}}{1 + A_2 \cdot A_{aux}} + V_{sw} \cdot A_{aux} \cdot A_2$$

$$V_{os, in, eff} \approx V_{os1} / A_2 A_{aux} + V_{os2} / A_1 A_2 + \frac{V_{sw} \cdot A_{aux}}{A_1}$$

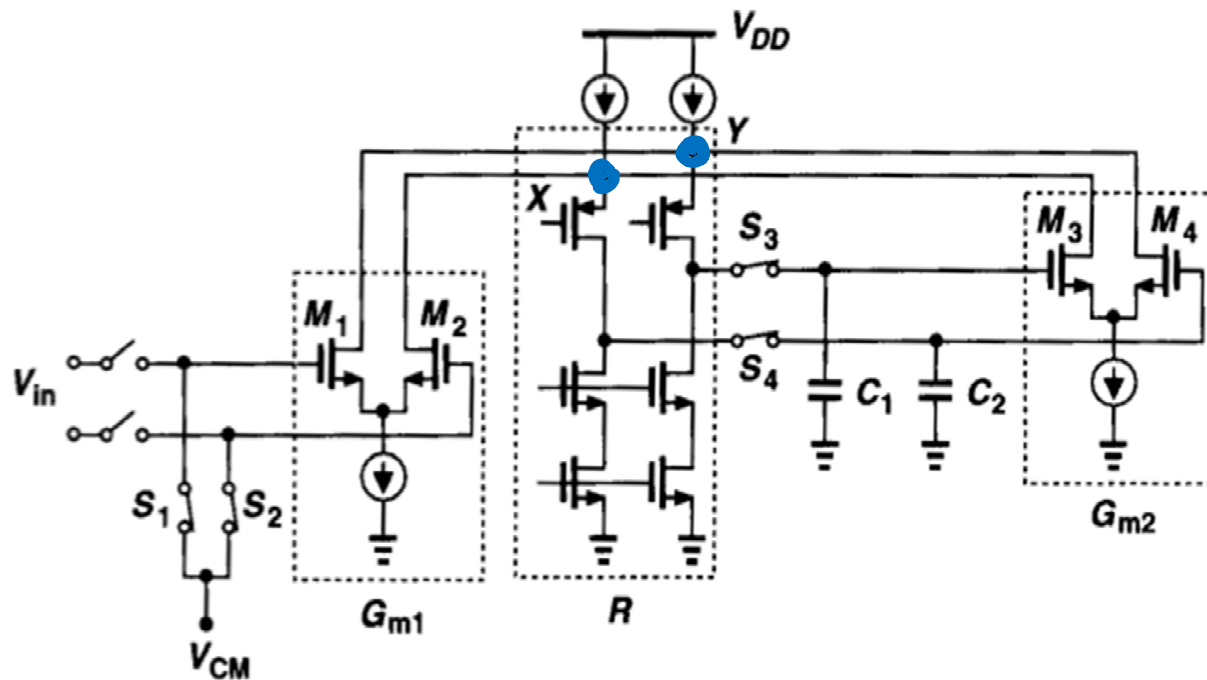
(normal operation)

usually, keep  $A_{aux} < A_1$

- ◆ For mismatch in charge injection when turning  $S_3$  and  $S_4$  OFF  
giving  $V_{sw}$ , a slight differential voltage error at  $V_{aux}$  input

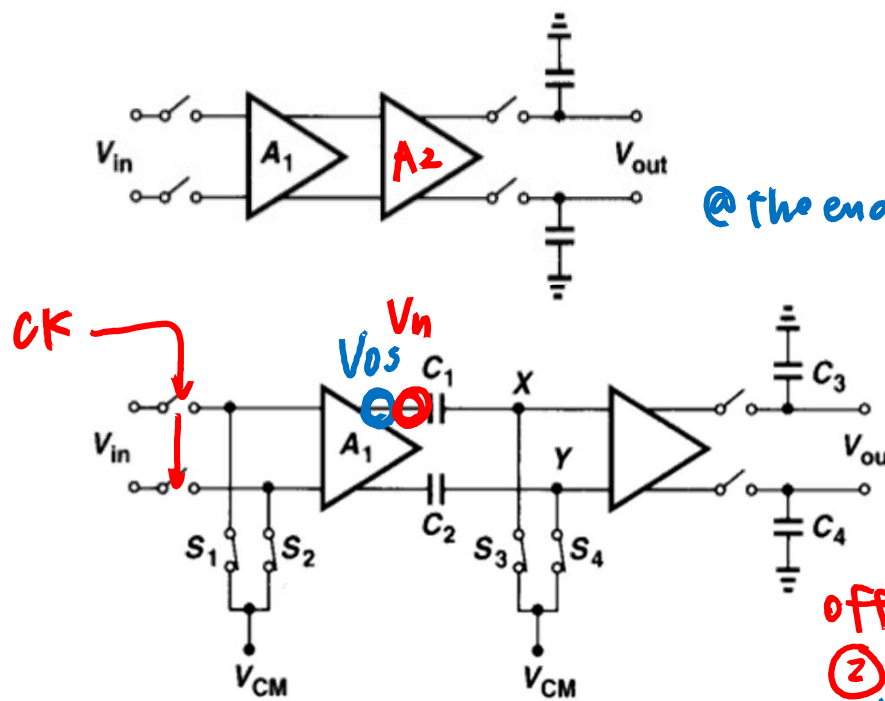
# Offset Cancellation Techniques *One implementation*

- ◆ The additional stage  $A_2$  may not be allowed
- ◆ How to achieve “voltage addition”? *No, it's performed in cur. domain*



# Reduction of Noise by Offset Cancellation

- ◆ For a cascade of two amplifiers in the front-end of a sampling system
  - Noise/offset of  $A_1$  corrupts  $V_{in}$  directly

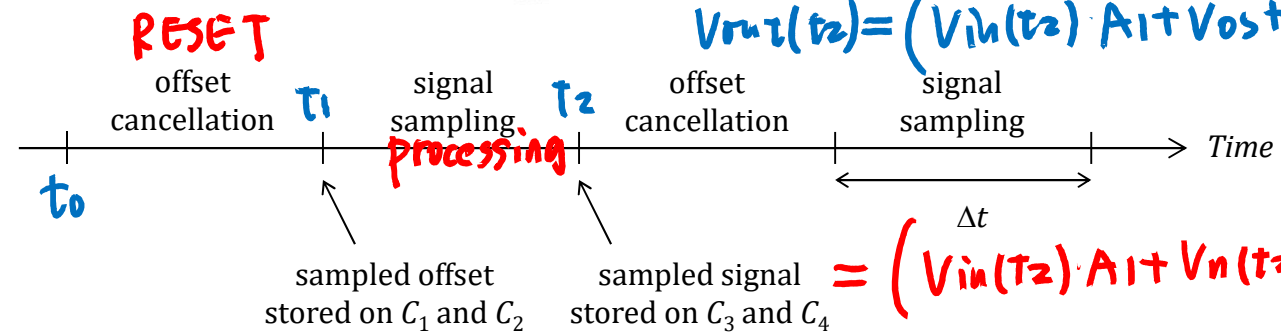


with CK controlling SW's  
the ckt has two-phase operation  
@ the end of sig. processing phase

$V_{out}(t_2) = V_{in}(t_2) \cdot A_1 \cdot A_2$  ideally

① offset  
 $V_{out}(t_2) = (V_{in}(t_2) \cdot A_1 + V_{os} - V_c) \cdot A_2$   
ideally, with perfect can  
 $= V_{in}(t_2) \cdot A_1 \cdot A_2$

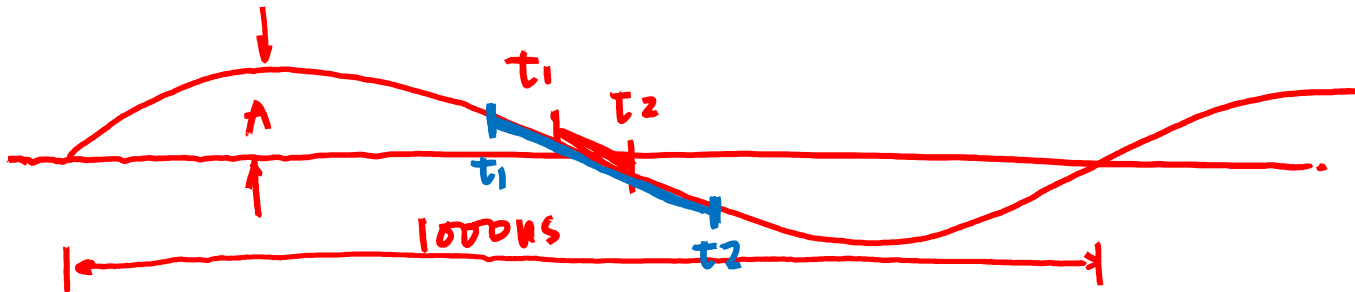
offset +  
② noise  
 $V_{out}(t_2) = (V_{in}(t_2) \cdot A_1 + V_{os} + V_n(t_2) - V_c) \cdot A_2$   
 $\downarrow$   
 $V_{os}(t_1) + V_n(t_1)$   
 $= (V_{in}(t_2) \cdot A_1 + V_n(t_2) - V_n(t_1)) \cdot A_2$



# Reduction of Noise by Offset Cancellation

- ◆ Assume  $\Delta t = 10 \text{ ns} = t_2 - t_1 \rightarrow 50 \text{ MHz of } \omega$
- ◆ Consider two noise components at 1 MHz and 10 MHz respectively
- ◆ During the 10 ns

$$V_{n1}(\tau) = A \sin(2\pi \cdot 10 \text{M} \cdot \tau)$$



$$\begin{aligned} \max(V_n(t_2) - V_n(t_1)) &= 6.3\% \cdot A \\ \max(V_n(t_2) - V_n(t_1)) &= 63\% \cdot A \end{aligned} \quad \left. \vphantom{\begin{aligned} \max(V_n(t_2) - V_n(t_1)) &= 6.3\% \cdot A \\ \max(V_n(t_2) - V_n(t_1)) &= 63\% \cdot A \end{aligned}} \right\} \text{high-pass filtering effect}$$

## Correlated double sampling (CDS)

- Two consecutive sampling operations with small  $\Delta t$  that low-frequency noise component cannot vary significantly